

Single N-channel MOSFET

ELM13410CA-S

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General description

ELM13410CA-S uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and operation with gate voltages as low as 1.8V.

Features

- $V_{ds}=30V$
- $I_d=5.8A$ ($V_{gs}=10V$)
- $R_{ds(on)} < 28m\Omega$ ($V_{gs}=10V$)
- $R_{ds(on)} < 33m\Omega$ ($V_{gs}=4.5V$)
- $R_{ds(on)} < 52m\Omega$ ($V_{gs}=2.5V$)
- $R_{ds(on)} < 70m\Omega$ ($V_{gs}=1.8V$)

Maximum absolute ratings

Parameter	Symbol	Limit	Unit	Note	
Drain-source voltage	V_{ds}	30	V		
Gate-source voltage	V_{gs}	± 12	V		
Continuous drain current	I_d	$T_a=25^\circ C$	5.8	A	1
		$T_a=70^\circ C$	4.9		
Pulsed drain current	I_{dm}	30	A	2	
Power dissipation	P_d	$T_a=25^\circ C$	1.4	W	1
		$T_a=70^\circ C$	1.0		
Junction and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ C$		

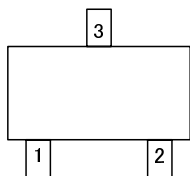
Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-ambient	$t \leq 10s$	$R\theta_{ja}$	65	90	$^\circ C/W$	1
Maximum junction-to-ambient	Steady-state		85	125	$^\circ C/W$	
Maximum junction-to-lead	Steady-state	$R\theta_{jl}$	43	60	$^\circ C/W$	3

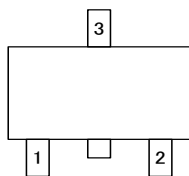
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Pin configuration

SOT-23 (TOP VIEW)



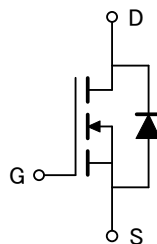
(Without extra bar)



(With extra bar)

Pin No.	Pin name
1	GATE
2	SOURCE
3	DRAIN

Circuit



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Electrical characteristics

Ta=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	BVdss	Id=250 μA, Vgs=0V	30			V
Zero gate voltage drain current	Idss	Vds=24V			1	μA
		Vgs=0V		Tj=55°C	5	
Gate-body leakage current	Igss	Vds=0V, Vgs=±12V			100	nA
Gate threshold voltage	Vgs(th)	Vds=Vgs, Id=250 μA	0.5	0.8	1.0	V
On state drain current	Id(on)	Vgs=4.5V, Vds=5V	30			A
Static drain-source on-resistance	Rds(on)	Vgs=10V		23	28	mΩ
		Id=5.8A	Tj=125°C	29	39	
		Vgs=4.5V, Id=5A		26	33	mΩ
		Vgs=2.5V, Id=4A		35	42	mΩ
		Vgs=1.8V, Id=3A		54	72	mΩ
Forward transconductance	Gfs	Vds=5V, Id=5A	12	17		S
Diode forward voltage	Vsd	Is=1A, Vgs=0V		0.66	1.00	V
Max. body-diode continuous current	Is				2.5	A
DYNAMIC PARAMETERS						
Input capacitance	Ciss			767		pF
Output capacitance	Coss	Vgs=0V, Vds=15V, f=1MHz		111		pF
Reverse transfer capacitance	Crss			82		pF
Gate resistance	Rg	Vgs=0V, Vds=0V, f=1MHz		1.3		Ω
SWITCHING PARAMETERS						
Total gate charge	Qg			10.0		nC
Gate-source charge	Qgs	Vgs=4.5V, Vds=15V, Id=5.8A		1.2		nC
Gate-drain charge	Qgd			3.1		nC
Turn-on delay time	td(on)			5.0		ns
Turn-on rise time	tr	Vgs=10V, Vds=15V		5.5		ns
Turn-off delay time	td(off)	RI=2.7 Ω, Rgen=6 Ω		39.0		ns
Turn-off fall time	tf			4.7		ns
Body diode reverse recovery time	trr	If=5A, dl/dt=100A/μs		15.0		ns
Body diode reverse recovery charge	Qrr	If=5A, dl/dt=100A/μs		7.1		nC

NOTE :

- The value of Rθja is measured with the device mounted on 1in² FR-4 board of 2oz. Copper, in still air environment with Ta=25°C. The value in any given applications depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The Rθja is the sum of the thermal impedance from junction to lead Rθjl and lead to ambient.
- The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5%max.
- These tests are performed with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with Ta=25°C. The SOA curve provides a single pulse rating.

Typical electrical and thermal characteristics

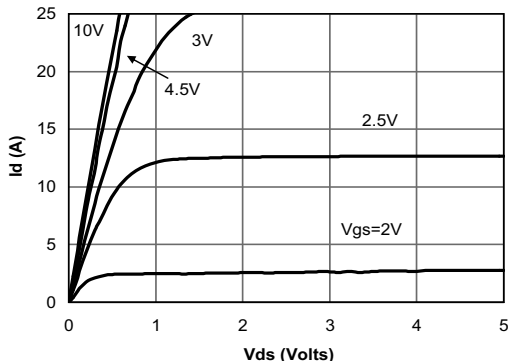


Fig 1: On-Region Characteristics

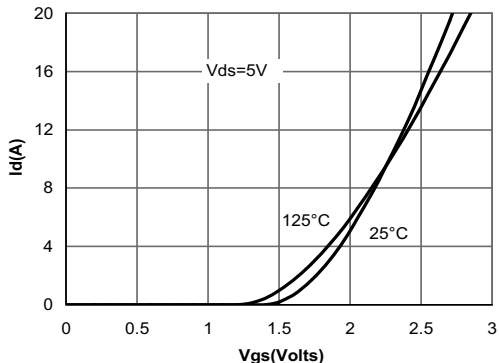


Figure 2: Transfer Characteristics

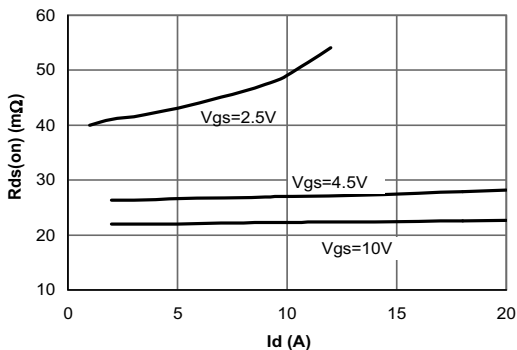


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

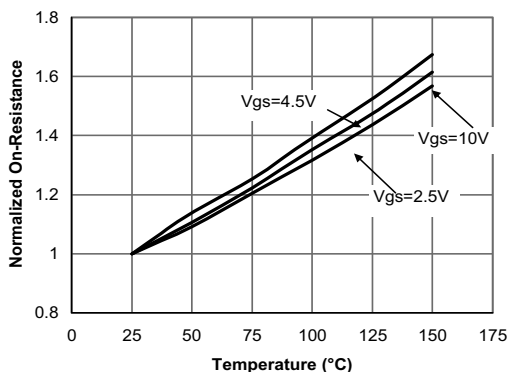


Figure 4: On-Resistance vs. Junction Temperature

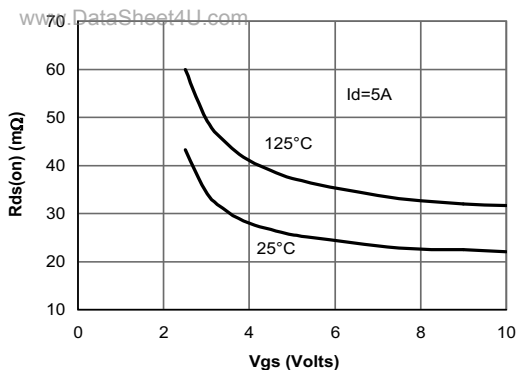


Figure 5: On-Resistance vs. Gate-Source Voltage

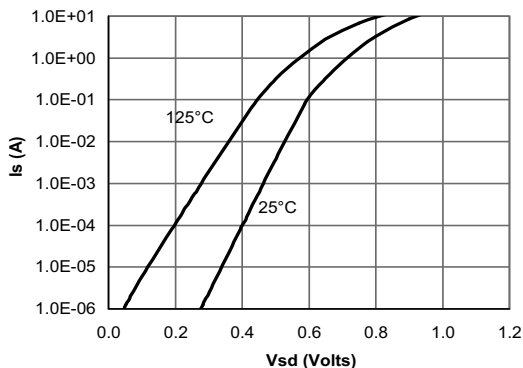


Figure 6: Body-Diode Characteristics

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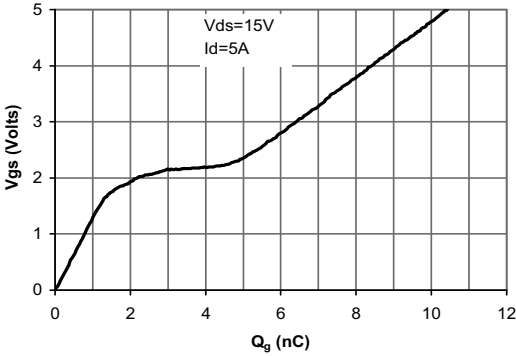


Figure 7: Gate-Charge Characteristics

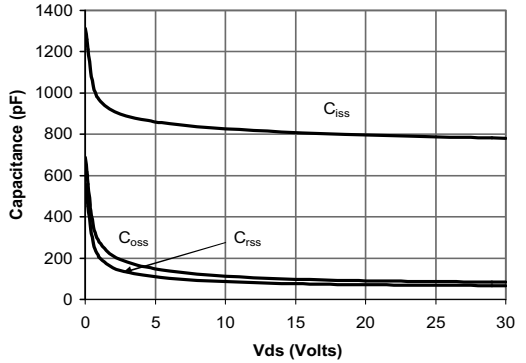


Figure 8: Capacitance Characteristics

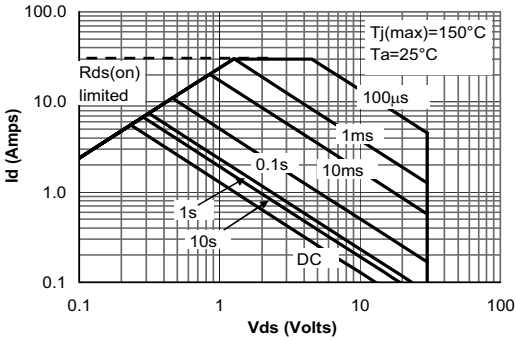


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

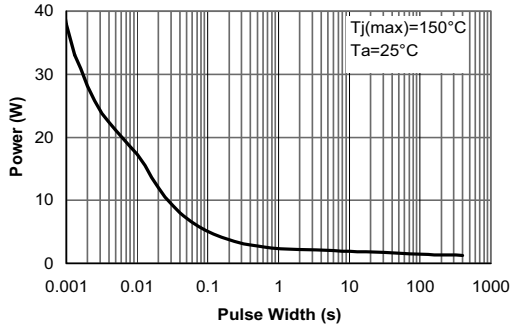


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

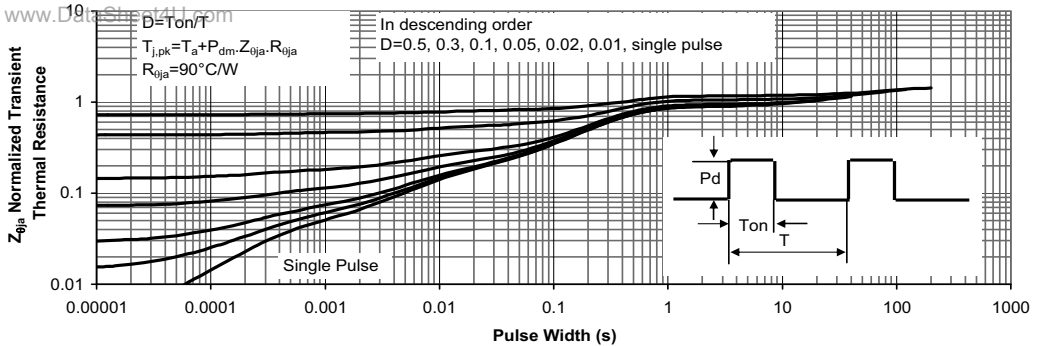


Figure 11: Normalized Maximum Transient Thermal Impedance